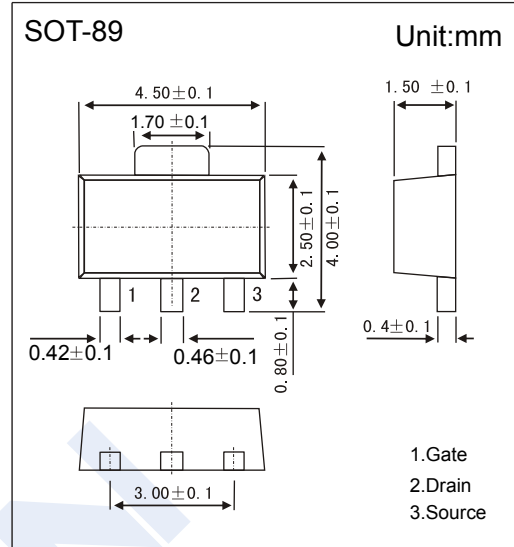
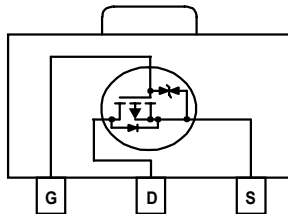


P-Channel MOSFET

XP162A11

■ Features

- $V_{DS} (V) = -30V$
- $I_D = -2.5 A (V_{GS} = -10V)$
- $R_{DS(ON)} < 150m\Omega (V_{GS} = -10V)$
- $R_{DS(ON)} < 280m\Omega (V_{GS} = -4.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-2.5	A
Pulsed Drain Current	I_{DM}	-10	
Reverse Drain Current	I_{DR}	-2.5	
Power Dissipation	P_D	2	W
Thermal Resistance, Junction- to-Ambient	R_{thJA}	62.5	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

P-Channel MOSFET

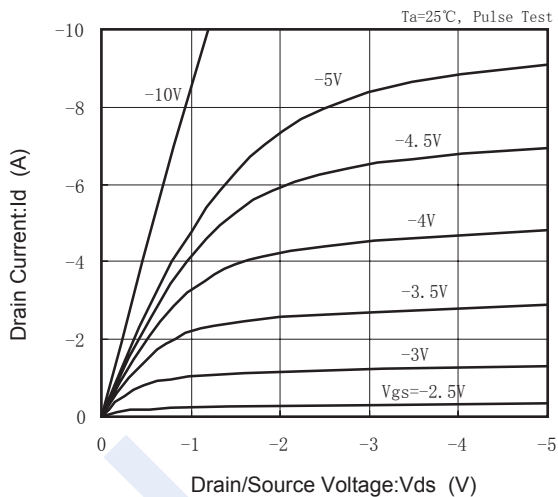
XP162A11

■ Electrical Characteristics Ta = 25°C

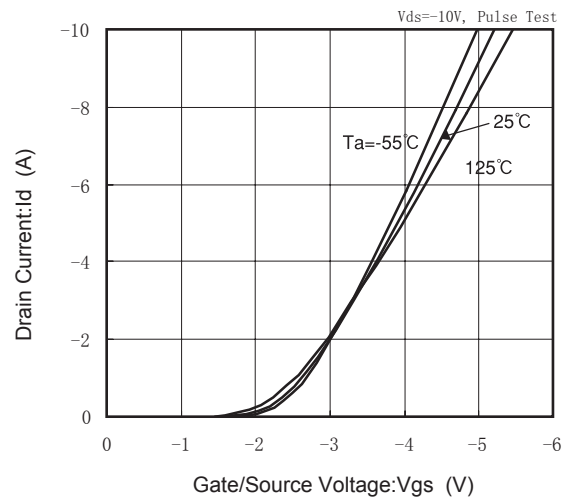
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{bss}	I _D =-250 μA, V _{GS} =0V	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-10	μA
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{GS} =-10V, I _D =-1mA	-1		-2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-1.5A			150	mΩ
		V _{GS} =-4.5V, I _D =-1.5A			280	
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-1.5A		25		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-10V, f=1MHz		280		pF
Output Capacitance	C _{oss}			200		
Reverse Transfer Capacitance	C _{rss}			90		
Turn-On DelayTime	t _{d(on)}		V _{GS} =-5V, V _{DS} =-10V, I _D =-1.5A		10	
Turn-On Rise Time	t _r			30		
Turn-Off DelayTime	t _{d(off)}			20		
Turn-Off Fall Time	t _f			35		
Diode Forward Voltage	V _{SD}	I _S =-2.5A, V _{GS} =0V			-1.1	V

■ Typical Characteristics

Drain Current vs. Drain/Source Voltage

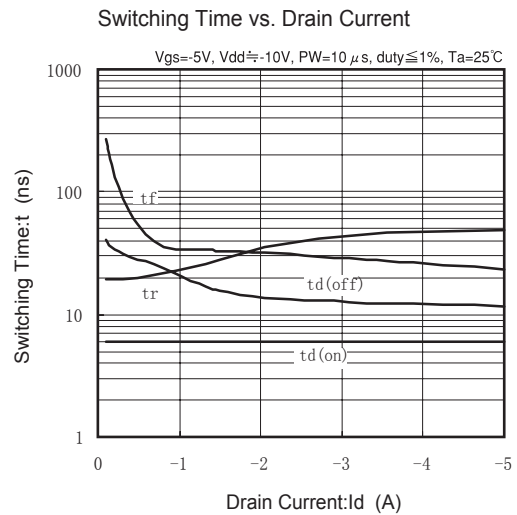
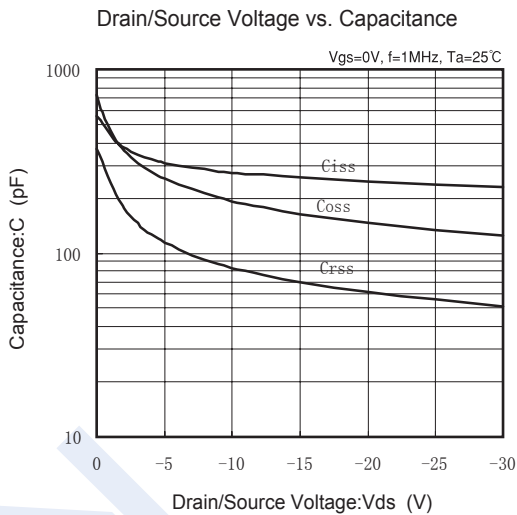
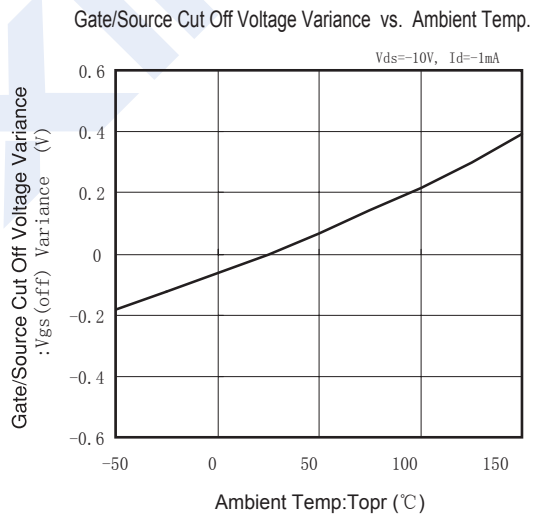
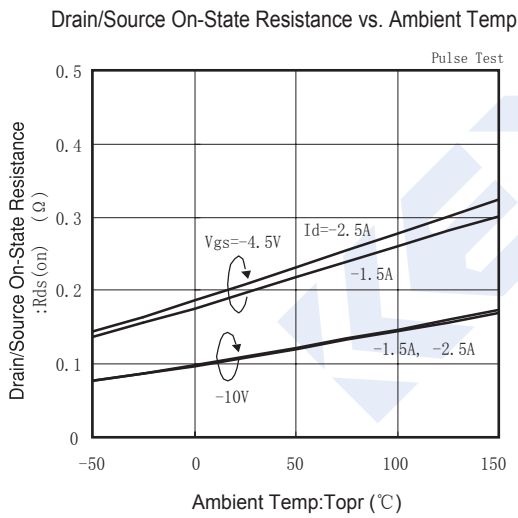
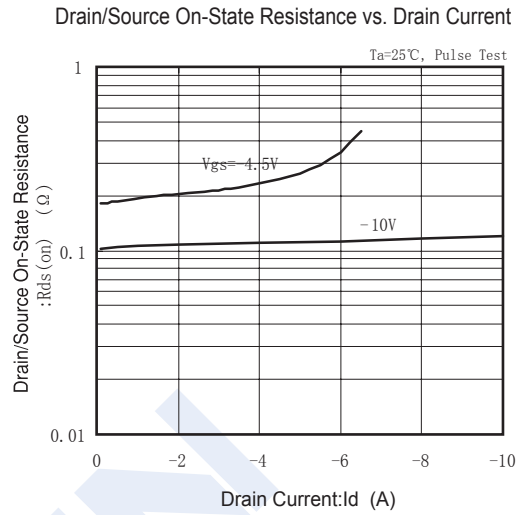
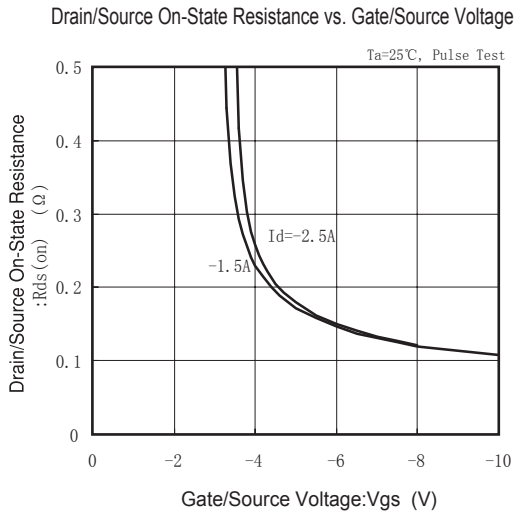


Drain Current vs. Gate/Source Voltage



P-Channel MOSFET XP162A11

■ Typical Characteristics



P-Channel MOSFET XP162A11

■ Typical Characteristics

